

HTIRC-02-013



December 10, 2003

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/660,914 09/12/03 |
Chao-Peng Chen et al.
METHOD TO PRINT PHOTORESIST LINES
WITH NEGATIVE SIDEWALLS
| _____ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

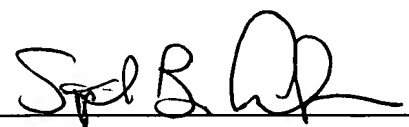
The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on December 19, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 12/19/03

U.S. Patent 5,310,626 to Fernandes et al., "Method for Forming a Patterned Layer Using Dielectric Materials as a Light-Sensitive Material," teaches using a tilt angle in photolithography.

U.S. Patent 6,504,675 to Shukh et al., "Perpendicular Magnetic Recording Heads with Write Pole Shaped to Reduce Skew Effects During Writing," discloses a trapezoidal write pole.

U.S. Patent 6,255,035 to Minter et al., "Method of Creating Optimal Photoresist Structures Used in the Manufacture of Metal T-Gates for High-Speed Semiconductor Devices," describes two photoresist layers exposed to e-beam to form negative resist sidewalls.

U.S. Patent 4,238,559 to Feng et al., "Two Layer Resist System," teaches that undercut resist profiles are easily attainable using e-beam lithography.

Sincerely

A handwritten signature in black ink, appearing to read "S. B. Ackerman", with a long horizontal flourish extending to the right.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

Document Number (Sequence)

Application Number

HTIRC-02-013

10/660,914

Applicant

Chao-Peng Chen et al.

Filing Date

09/12/03

Group Art Unit

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
	5310626	5/10/94	Fernandes et al.	430	327	3/1/93
	6504675	1/7/03	Shukh et al.	360	125	1/12/01
	6255035	7/3/01	Minter et al.	430	312	3/17/99
	4238559	12/9/80	Feng et al.	430	156	8/24/78

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.